

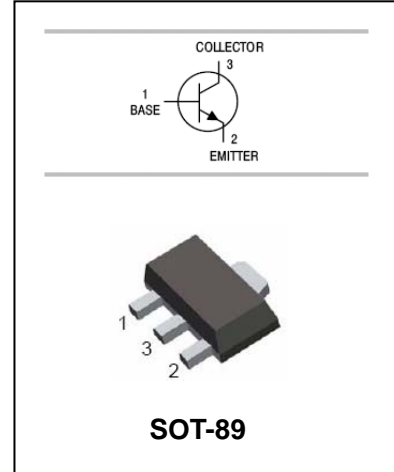


## High Voltage Fast Switching NPN Power Transistor

**3DD13002**

### FEATURES

- $P_C=1W$ (Mounted on ceramic substrate).
- High speed switching.
- Small flat package.



### APPLICATIONS

- High voltage switch mode application.

### ORDERING INFORMATION

Type No.	Marking	Package Code
3DD13002	13002	SOT-89

### MAXIMUM RATING @ $T_a=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	600	V
$V_{CEO}$	Collector-Emitter Voltage	400	V
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_C$	Collector Current -Continuous	1	A
$P_C$	Collector Dissipation	1.25	W
$T_j, T_{stg}$	Junction and Storage Temperature	-55 to +150	$^\circ\text{C}$



## High Voltage Fast Switching NPN Power Transistor

### 3DD13002

#### ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	600			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	400			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	6			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=600V, I_E=0$			100	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=6V, I_C=0$			100	$\mu A$
DC current gain	$h_{FE}$	$V_{CE}=10V, I_C=200mA$	9		40	
		$V_{CE}=10V, I_C=250\mu A$	5			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=200mA, I_B=40mA$			0.8	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=200mA, I_B=40mA$			1.1	V
Transition frequency	$f_T$	$V_{CE}=10V, I_C=100mA, f=1MHz$	5			MHz
Fall time	$t_f$	$I_C=1A, I_{B1}=I_{B2}=0.2A, V_{CC}=100V$			0.5	$\mu S$
Storage time	$t_s$				2.5	$\mu S$

#### CLASSIFICATION OF $h_{FE(1)}$

Range	9-15	15-20	20-25	25-30	30-35	35-40

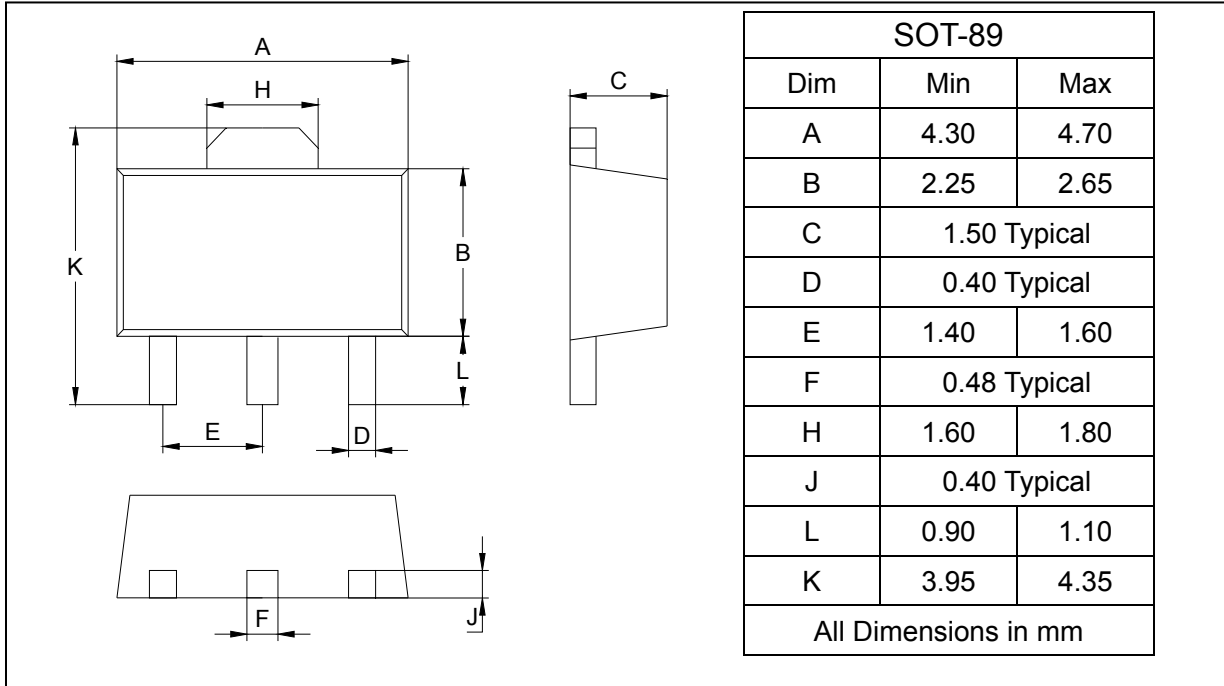
# High Voltage Fast Switching NPN Power Transistor

## 3DD13002

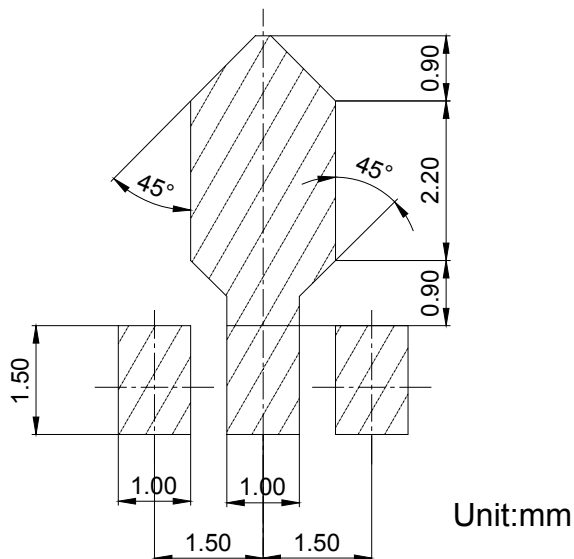
### PACKAGE OUTLINE

Plastic surface mounted package

SOT-89



### SOLDERING FOOTPRINT



### PACKAGE INFORMATION

Device	Package	Shipping
3DD13002	SOT-89	1000/Tape&Reel